

# MJ15023 (PNP), MJ15025 (PNP)

## Silicon Power Transistors

The MJ15023 and MJ15025 are power transistors designed for high power audio, disk head positioners and other linear applications.

### Features

- High Safe Operating Area
- High DC Current Gain
- Complementary to MJ15022 (NPN), MJ15024 (NPN)
- These Devices are Pb-Free and are RoHS Compliant\*

### MAXIMUM RATINGS

| Rating                                                                                    | Symbol         | Value       | Unit                     |
|-------------------------------------------------------------------------------------------|----------------|-------------|--------------------------|
| Collector-Emitter Voltage<br>MJ15023<br>MJ15025                                           | $V_{CEO}$      | 200<br>250  | Vdc                      |
| Collector-Base Voltage<br>MJ15023<br>MJ15025                                              | $V_{CBO}$      | 350<br>400  | Vdc                      |
| Emitter-Base Voltage                                                                      | $V_{EBO}$      | 5           | Vdc                      |
| Collector-Emitter Voltage                                                                 | $V_{CEX}$      | 400         | Vdc                      |
| Collector Current – Continuous (Note 1)                                                   | $I_C$          | 16          | Adc                      |
| Collector Current – Peak (Note 1)                                                         | $I_{CM}$       | 30          | Adc                      |
| Base Current – Continuous                                                                 | $I_B$          | 5           | Adc                      |
| Total Device Dissipation<br>@ $T_C = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$          | 250<br>1.43 | W<br>W/ $^\circ\text{C}$ |
| Operating and Storage Junction<br>Temperature Range                                       | $T_J, T_{stg}$ | -65 to +200 | $^\circ\text{C}$         |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle  $\leq 10\%$ .

### THERMAL CHARACTERISTICS

| Characteristics                      | Symbol          | Max  | Unit               |
|--------------------------------------|-----------------|------|--------------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 0.70 | $^\circ\text{C/W}$ |

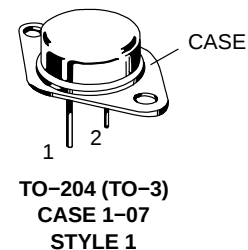
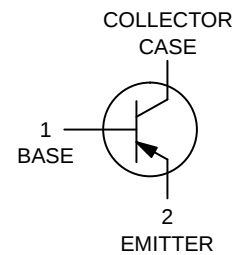
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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## 16 AMPERES SILICON POWER TRANSISTORS 200 – 250 VOLTS, 250 WATTS



### MARKING DIAGRAM



MJ1502x = Device Code  
x = 3 or 5  
G = Pb-Free Package  
A = Assembly Location  
Y = Year  
WV = Work Week  
MEX = Country of Origin

### ORDERING INFORMATION

| Device   | Package          | Shipping         |
|----------|------------------|------------------|
| MJ15023G | TO-204 (Pb-Free) | 100 Units / Tray |
| MJ15025G | TO-204 (Pb-Free) | 100 Units / Tray |

## MJ15023 (PNP), MJ15025 (PNP)

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic                                                                                                                                                                                        | Symbol         | Min        | Max        | Unit            |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------|------------|------------|-----------------|
| <b>OFF CHARACTERISTICS</b>                                                                                                                                                                            |                |            |            |                 |
| Collector-Emitter Sustaining Voltage (Note 2)<br>( $I_C = 100\text{ mAdc}$ , $I_B = 0$ )<br>MJ15023<br>MJ15025                                                                                        | $V_{CEO(sus)}$ | 200<br>250 | –<br>–     | –               |
| Collector Cutoff Current<br>( $V_{CE} = 200\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ )<br>MJ15023<br>( $V_{CE} = 250\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ )<br>MJ15025                    | $I_{CEX}$      | –<br>–     | 250<br>250 | $\mu\text{Adc}$ |
| Collector Cutoff Current<br>( $V_{CE} = 150\text{ Vdc}$ , $I_B = 0$ )<br>MJ15023<br>( $V_{CE} = 200\text{ Vdc}$ , $I_B = 0$ )<br>MJ15025                                                              | $I_{CEO}$      | –<br>–     | 500<br>500 | $\mu\text{Adc}$ |
| Emitter Cutoff Current<br>( $V_{CE} = 5\text{ Vdc}$ , $I_B = 0$ )<br>Both                                                                                                                             | $I_{EBO}$      | –          | 500        | $\mu\text{Adc}$ |
| <b>SECOND BREAKDOWN</b>                                                                                                                                                                               |                |            |            |                 |
| Second Breakdown Collector Current with Base Forward Biased<br>( $V_{CE} = 50\text{ Vdc}$ , $t = 0.5\text{ s}$ (non-repetitive))<br>( $V_{CE} = 80\text{ Vdc}$ , $t = 0.5\text{ s}$ (non-repetitive)) | $I_{S/b}$      | 5<br>2     | –<br>–     | Adc             |
| <b>ON CHARACTERISTICS</b>                                                                                                                                                                             |                |            |            |                 |
| DC Current Gain<br>( $I_C = 8\text{ Adc}$ , $V_{CE} = 4\text{ Vdc}$ )<br>( $I_C = 16\text{ Adc}$ , $V_{CE} = 4\text{ Vdc}$ )                                                                          | $h_{FE}$       | 15<br>5    | 60<br>–    | –               |
| Collector-Emitter Saturation Voltage<br>( $I_C = 8\text{ Adc}$ , $I_B = 0.8\text{ Adc}$ )<br>( $I_C = 16\text{ Adc}$ , $I_B = 3.2\text{ Adc}$ )                                                       | $V_{CE(sat)}$  | –<br>–     | 1.4<br>4.0 | Vdc             |
| Base-Emitter On Voltage<br>( $I_C = 8\text{ Adc}$ , $V_{CE} = 4\text{ Vdc}$ )                                                                                                                         | $V_{BE(on)}$   | –          | 2.2        | Vdc             |
| <b>DYNAMIC CHARACTERISTICS</b>                                                                                                                                                                        |                |            |            |                 |
| Current-Gain – Bandwidth Product<br>( $I_C = 1\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f_{test} = 1\text{ MHz}$ )                                                                                   | $f_T$          | 4          | –          | MHz             |
| Output Capacitance<br>( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f_{test} = 1\text{ MHz}$ )                                                                                                            | $C_{ob}$       | –          | 600        | pF              |

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

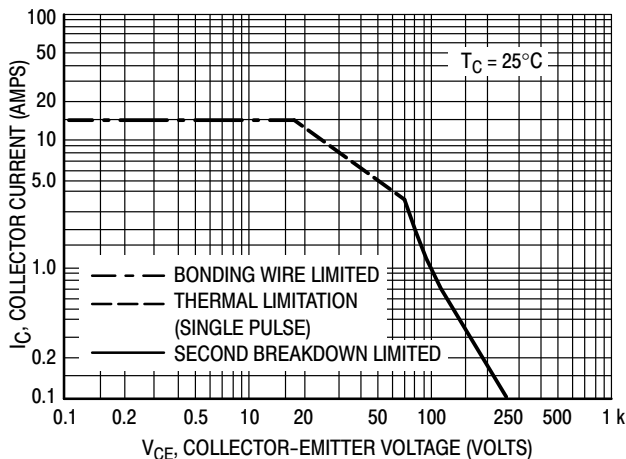


Figure 1. Active-Region Safe Operating Area

There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on  $T_{J(pk)} = 200^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

# MJ15023 (PNP), MJ15025 (PNP)

## TYPICAL CHARACTERISTICS

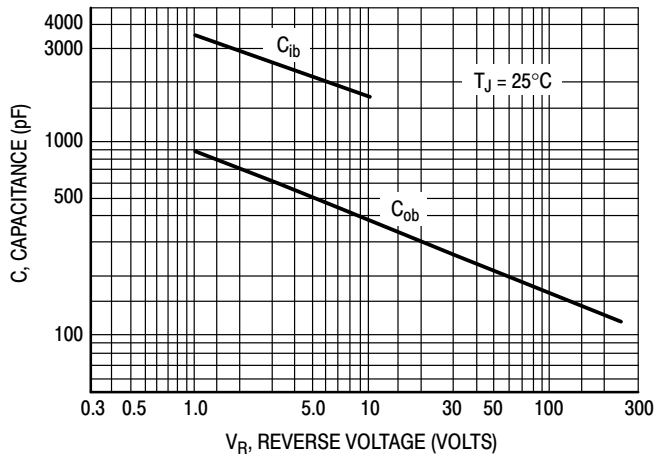


Figure 2. Capacitances

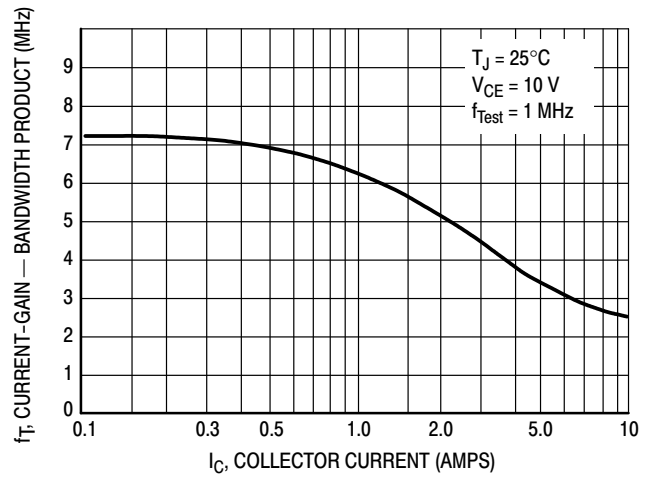


Figure 3. Current-Gain - Bandwidth Product

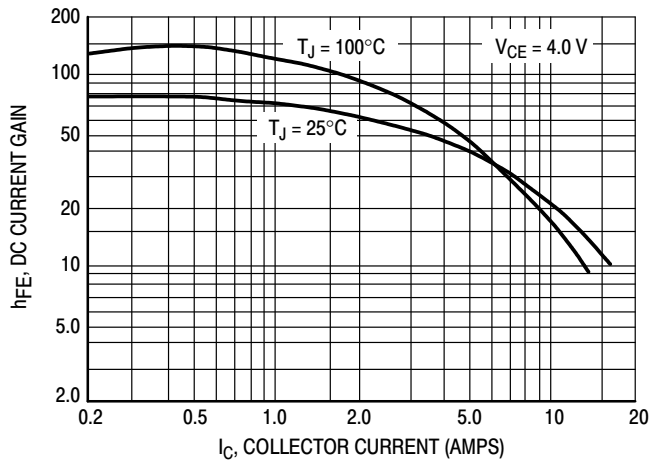


Figure 4. DC Current Gain

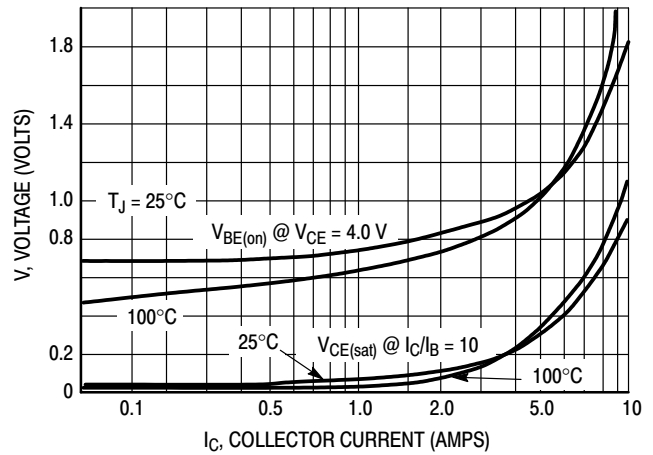
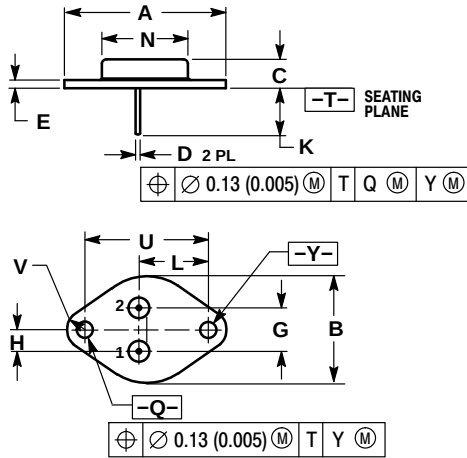


Figure 5. "On" Voltages

# MJ15023 (PNP), MJ15025 (PNP)

## PACKAGE DIMENSIONS

### TO-204 (TO-3) CASE 1-07 ISSUE Z



#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

| DIM | INCHES    |       | MILLIMETERS |       |
|-----|-----------|-------|-------------|-------|
|     | MIN       | MAX   | MIN         | MAX   |
| A   | 1.550 REF |       | 39.37 REF   |       |
| B   | ---       | 1.050 | ---         | 26.67 |
| C   | 0.250     | 0.335 | 6.35        | 8.51  |
| D   | 0.038     | 0.043 | 0.97        | 1.09  |
| E   | 0.055     | 0.070 | 1.40        | 1.77  |
| G   | 0.430 BSC |       | 10.92 BSC   |       |
| H   | 0.215 BSC |       | 5.46 BSC    |       |
| K   | 0.440     | 0.480 | 11.18       | 12.19 |
| L   | 0.665 BSC |       | 16.89 BSC   |       |
| N   | ---       | 0.830 | ---         | 21.08 |
| Q   | 0.151     | 0.165 | 3.84        | 4.19  |
| U   | 1.187 BSC |       | 30.15 BSC   |       |
| V   | 0.131     | 0.188 | 3.33        | 4.77  |

#### STYLE 1:

- PIN 1. BASE
- EMITTER
- COLLECTOR

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